**Application No.: 10/681,443**

## AMENDMENT TO THE CLAIMS

1-33. (Cancelled)

34. (Previously presented) The semiconductor light-emitting device according to claim 35, wherein said divided electrode is in contact with said n-type nitride semiconductor portion.

35. (Previously presented) A semiconductor light-emitting device comprising:

an n-side electrode;

a p-side electrode;

an n-type nitride semiconductor portion electrically connected to said n-side electrode;

a p-type nitride semiconductor portion electrically connected to said p-side electrode; and

an active layer, sandwiched between said n-type nitride semiconductor portion and said p-type nitride semiconductor portion, for generating emission light,

wherein said n-side electrode is formed on one side of said p-side electrode and is a divided electrode comprising a plurality of conductive members spaced apart from each other,

said p-side electrode is formed in a linear shape in plan view, and

said n-side electrode is formed so as to be entirely parallel to said p-side electrode.

36. (Previously presented) The semiconductor light-emitting device according to claim 35, wherein said divided electrode is divided in a longitudinal direction of said p-side electrode.





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37. (Previously presented) The semiconductor light-emitting device according to claim 35, further comprising a substrate, wherein,

said n-type nitride semiconductor portion is provided on a surface of the substrate and is sandwiched between said each divided electrode and said substrate.

38. (Previously presented) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed at an angle of 90° to said p-type electrode in plan view.

39. (Previously presented) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed at an angle of $\theta$ ($0° < \theta < 90°$) to said p-type electrode in plan view.

40. (Previously presented) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed in a zigzag shape.

41. (Previously presented) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed in a curved shape.

42. (Previously presented) A semiconductor light-emitting device comprising:

an n-side electrode;



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a p-side electrode having a striped pattern;

an n-type nitride semiconductor portion electrically connected to said n-side electrode;

a p-type nitride semiconductor portion electrically connected to said p-side electrode; and

an active layer, sandwiched between said n-type nitride semiconductor portion and said p-type nitride semiconductor portion, for generating emission light,

wherein said n-side electrode is a divided electrode comprising a plurality of conductive members spaced apart from each other,

said plurality of conductive members sandwich said p-side electrode in plan view, and

said plurality of conductive members are formed so as to be asymmetrical in plan view with respect to a longitudinal direction of said p-side electrode.

43. (Canceled)

44. (Previously presented) The semiconductor light-emitting device according to claim 42, wherein one of said divided electrodes is not disposed at a portion opposite to the other divided electrode with said p-side electrode being interposed therebetween.

45. (Previously presented) The semiconductor light-emitting device according to claim 44, wherein said divided electrodes are adapted such that each have an overlapping portion that overlaps the other at their ends adjacent to each other in a direction perpendicular to the p-side electrode in the plane thereof in plan view.





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46. (Previously presented) A semiconductor light-emitting device comprising:

an n-side electrode;

a p-side electrode;

an n-type nitride semiconductor portion electrically connected to said n-side electrode;

a p-type nitride semiconductor portion electrically connected to said p-side electrode;

an active layer, sandwiched between said n-type nitride semiconductor portion and said p-type nitride semiconductor portion, for generating emission light, and

a substrate,

wherein said n-side electrode is a divided electrode comprising a plurality of conductive members spaced apart from each other,

said substrate is conductive,

said n-type nitride semiconductor portion is provided on a surface of said substrate, and

one of said plurality of conductive members is provided on a rear surface of said substrate.

47. (Previously presented) The semiconductor light-emitting device according to claim 46, wherein said the other divided electrode is in contact with said n-type nitride semiconductor portion.

48-51. (Canceled)

52. (New) The semiconductor light-emitting device according to claim 42, wherein said divided electrode is in contact with said n-type nitride semiconductor portion.





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